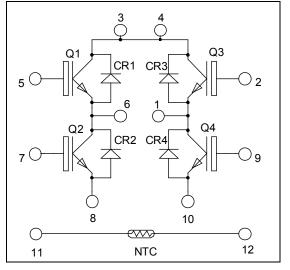
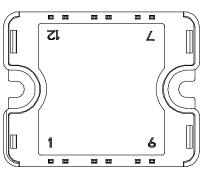


Full bridge High speed Trench + Field Stop IGBT4 Power Module

$V_{CES} = 650V$ $I_C = 75A$ @ Tc = 60°C





Pins 3/4 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

• High speed Trench + Field Stop IGBT 4 Technology

- Low voltage drop
- Low leakage current
- Low switching losses
- RBSOA and SCSOA rated
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

All ratings @ T_j = 25°C unless otherwise specified

Absolute maximum ratings (per IGBT)

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Voltage		650	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	100	
I _C	Continuous Conector Current	$T_C = 60^{\circ}C$	75	Α
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	200	
V _{GE}	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation		250	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	150A @ 600V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 650V$				100	μA
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.85	2.3	V
V _{CE(sat)}		$I_C = 75A$	$T_{j} = 150^{\circ}C$		2.2		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.2 \text{ mA}$		4.2	5.1	5.6	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				200	nA

Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		4620		
C _{oes}	Output Capacitance	$V_{CE} = 25V$		160		pF
Cres	Reverse Transfer Capacitance	f = 1 MHz		137		
Q _G	Gate charge	$V_{GE} = 15V, I_C = 75A$ $V_{CE} = 480V$		440		nC
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)		19		
T _r	Rise Time	$V_{GE} = \pm 15V$		33		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 400V$ $I_C = 75A$		197		ns
$T_{\rm f}$	Fall Time	$R_G = 5\Omega$		21		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C)		19		
Tr	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 400V$		29		
T _{d(off)}	Turn-off Delay Time	$I_{\rm C} = 75 \text{A}$		227		ns
T _f	Fall Time	$R_G = 5\Omega$		22		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $T_i = 25^{\circ}C$		1.5		
-011		$V_{Bus} = 400V$ $T_i = 150^{\circ}C$		1.8		mJ
E_{off}	Turn off Energy	$I_{C} = 75A \qquad T_{i} = 25^{\circ}C$ $R_{G} = 5\Omega \qquad T_{i} = 150^{\circ}C$		1.25		
I _{sc}	Short Circuit data	$ \begin{array}{c} V_{GE} \leq \!\! 15V \; ; \; V_{Bus} = 400V \\ t_p \! \leq \!\! 5\mu s \; ; \; T_j = 150^\circ C \end{array} $		500		А
R _{thJC}	Junction to Case Thermal Resistance				0.6	°C/W

Diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions			Тур	Max	Unit
V _{RRM}	Peak Repetitive Reverse Voltage					650	V
I _{RM}	Reverse Leakage Current	$V_R = 650V$				100	μA
$I_{\rm F}$	DC Forward Current		$Tc = 25^{\circ}C$		75		А
Va	V_F Diode Forward Voltage $I_F = 75A$ $V_{GE} = 0V$		$T_i = 25^{\circ}C$		1.6	2	v
• F		$T_{i} = 150^{\circ}C$		1.5		v	
t _{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$		100		ns
ι _{rr}	Reverse Recovery Time		$T_{j} = 150^{\circ}C$		150		115
0	Reverse Recovery Charge	$V_{\rm p} = 400 V$	$T_j = 25^{\circ}C$		3.6		μC
Q _{rr}	Reverse Recovery Charge		$T_{j} = 150^{\circ}C$		7.6		μĊ
Err	Reverse Recovery Energy		$T_j = 25^{\circ}C$	0.85		mJ	
$r_{\rm II}$	Reverse Recovery Energy		$T_{j} = 150^{\circ}C$		1.8		1115
R _{thJC}	Junction to Case Thermal Resistance					0.98	°C/W

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Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

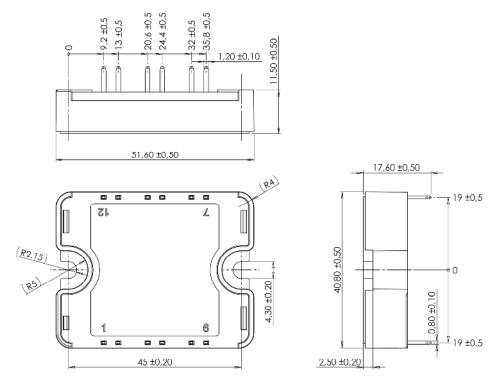
Symbol	Characteristic	,	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta B/B$		T _C =100°C		4		%
	D					

 $R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$ T: Thermistor temperature R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V _{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1 \text{ min}$, 50/60Hz					V
T _J	Operating junction temperature range			-40	175	
T _{JOP}	Recommended junction temperature under switching conditions			-40	T _J max -25	°C
T _{STG}	Storage Temperature Range			-40	125	C
T _C	Operating Case Temperature				100	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				80	g

Package outline (dimensions in mm)

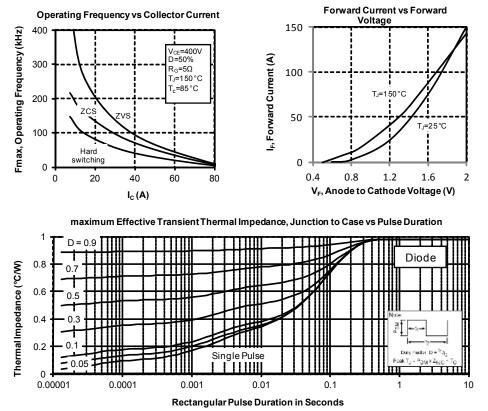


See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

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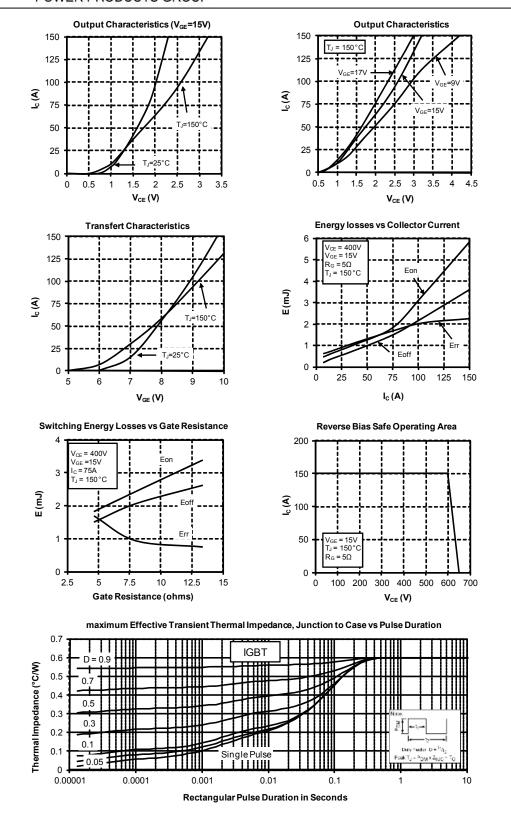
Typical performance curve



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